AEC-Q MEMORY EEPROM 16K bits (2048 X 8) HIGH TEMPERATURE AND AUTOMOTIVE EEPROM

DESCRIPTION

A24C16A provides 16384 bits of serial electrically erasable and programmable read-only memory (EEPROM), organized as 2048 words of 8 bits each.

The A24C16A is optimized for use in many industrial and commercial applications where low-power and low-voltage operation is essential.

The A24C16A is available in SOP8, TSSOP8, DFN8, SOT-25 and TSOT-25 packages.

AEC-Q100 Qualified is available in SOP8, TSSOP8, DFN8 and SOT-25 packages.

ORDERING INFORMATION

Package Type		Part Number				
SOP8						
AEC-Q100	M8	A24C16AM8VR-X				
SPQ: 2,500pcs/Reel						
TSSOP8						
AEC-Q100	TMX8	A24C16ATMX8VR-X				
SPQ: 3,000pcs/Reel						
DFN8						
AEC-Q100	J8	A24C16AJ8VR-X				
SPQ: 3,000pcs/Reel						
SOT-25						
AEC-Q100	E5	A24C16AE5VR-X				
SPQ: 3,000pcs/Reel						
TSOT-25	TE5	A24C16ATE5VR-X				
SPQ: 3,000pcs/Reel	_					
		perature, AEC-Q				
		40°C to +105°C				
Note	C : -40°C to +125°C					
11010		EC-Q100				
		gen Free Package				
	R: Tape & Reel					
AiT provides all Re	oHS pro	oHS products				

FEATURES

 Compatible with all I²C bidirectional data transfer protocol

Memory Array:

16K bits (2048X 8) of EEPROM

Page size: 16 bytes

Extended Temperature Range

B: -40°C to +105°C

C: -40°C to +125°C

Q:-40°C to +125°C (AEC-Q100 Certificated)

Single Supply Voltage and High Speed:

1MHz

Random and sequential Read modes

Write:

Byte Write within 3 ms

Page Write within 3 ms

Partial Page Writes Allowed

• Write Protect Pin for Hardware Data Protection

 Schmitt Trigger, Filtered Inputs for Noise Suppression

High-Reliability

Endurance: 4 Million Write Cycles

Data Retention: 100 Years

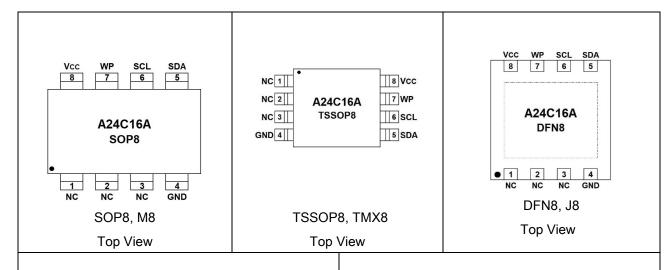
Enhanced ESD/Latch-up Protection

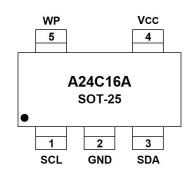
HBM 8000V

REV1.0Q - FEB 2024 RELEASED - -1

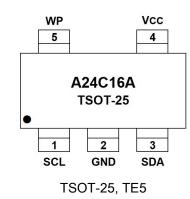


PIN DESCIPTION





SOT-25, E5 Top View



Top View

Pin#				
SOP8 / TSSOP8	SOT-25	Symbol	Туре	Functions
DFN8	TSOT-25			
1,2,3	-	NC	-	NC
4	2	GND	Р	Ground
5	3	SDA	I/O	Serial Data
6	1	SCL	I	Serial Clock Input
7	5	WP	I	Write Protect
8	4	Vcc	Р	Power Supply

REV1.0Q - FEB 2024 RELEASED - - 2 -

AEC-Q MEMORY EEPROM 16K bits (2048 X 8) HIGH TEMPERATURE AND AUTOMOTIVE EEPROM

ABSOLUTE MAXIMUM RATINGS

DC Supply Voltage	-0.3V ~ +6.5V
Input / Output Voltage	GND-0.3V ~ V _{CC} +0.3V
Storage Temperature	-65°C ~ +150°C
Electrostatic Pulse (Human Body Model)	8000V
Junction Temperature (T _{jmax})	+150°C

Stresses above may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the Electrical Characteristics is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

PIN CAPACITANCE

Applicable over recommended operating range from: $T_A = 25$ °C, f = 1.0MHz, $V_{CC} = +2.5$ V

Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit
Input/ Output Capacitance (SDA)	C _{I/O}	V _{I/O} =0V	-	-	8	pF
Input Capacitance (A0, A1, A2, SCL)	Cin	V _{IN} =0V	-	-	6	pF

DC ELECTRICAL CHARACTERISTICS

Applicable over recommended operating range, unless otherwise noted

A24C16A-B	$T_A = -40^{\circ}C$ to +105°C	V _{CC} = +1.7V to +5.5V@400kHz
A24C16A-C	$T_A = -40^{\circ}C$ to +125°C	Vcc = +2.5V to +5.5V@1MHz
A24C16A-Q	$T_A = -40^{\circ}C$ to +125°C	C _L =100 pF

Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit
Supply Current V _{CC} = 5.0V	I _{CCR}	Read at 400kHz	-	0.14	0.3	mA
Supply Current Vcc = 5.0V	Iccw	Write at 400kHz	-	0.28	0.5	mA
Supply Current V _{CC} = 5.0V	I _{SB}	$V_{IN} = V_{CC}$ or GND	-	0.03	2.0	μΑ
Input Leakage Current	ILI	$V_{IN} = V_{CC}$ or GND	-	0.10	1.0	μΑ
Output Leakage Current	ILO	V _{OUT} = V _{CC} or V _{SS}	-	0.05	1.0	μΑ
Input Low Level	V _{IL}	V _{CC} = 1.7V to 5.5V	-0.3	-	V _{CC} x 0.3	V
Input High Level	V _{IH}	V _{CC} = 1.7V to 5.5V	V _{CC} x0.7	-	V _{CC} + 0.3	V
Output Low Level V _{CC} = 1.7V	V _{OL1}	I _{OL} = 0.15mA	-	-	0.2	V
Output Low Level V _{CC} = 5.0V	V_{OL2}	I _{OL} = 3.0mA	-	-	0.4	V

REV1.0Q - FEB 2024 RELEASED - - 3 -

AEC-Q MEMORY EEPROM 16K bits (2048 X 8) HIGH TEMPERATURE AND AUTOMOTIVE EEPROM

AC ELECTRICAL CHARACTERISTICS (2)

Applicable over recommended operating range, unless otherwise noted

A24C16A-B	T _A = -40°C to +105°C	V _{CC} = +1.7V to +5.5V@400kHz
A24C16A-C	T _A = -40°C to +125°C	V _{CC} = +2.5V to +5.5V@1MHz
A24C16A-Q	T _A = -40°C to +125°C	C _L =100 pF

Danamatan	Or week al	1.7	V≤V _{CC} <2	2.5V	2.5	V≤Vcc<5	5.5V	11-4
Parameter	Symbol	Min.	Тур.	Max.	Min.	Тур.	Max.	Unit
Clock Frequency, SCL	fscL	-	-	400	-	-	1000	kHz
Clock Pulse Width Low	t _{LOW}	1.3	-	-	0.5	-	-	μs
Clock Pulse Width High	tніgн	0.6	-	-	0.26	-	-	μs
Noise Suppression Time	tı	-	-	50	-	-	50	ns
Clock Low to Data Out Valid	t _{AA}	ı	-	0.9	-	1	0.45	μs
Time the bus must be free before a new transmission can start	t BUF	1.3	-	-	0.5	1	-	μs
Start Hold Time	thd.sta	0.6	-	-	0.25	-	-	μs
Start Setup Time	t su.sta	0.6	-	-	0.25	-	-	μs
Data In Hold Time	thd.dat	0	-	-	0	-	-	μs
Data In Setup Time	t su.dat	100	-	-	100	-	-	ns
Inputs Rise Time (1)	t _R	-	-	0.3	-	-	0.12	μs
Inputs Fall Time (1)	t⊧	-	-	0.3	-	-	0.12	μs
Stop Setup Time	t su.sto	0.6	-	-	0.25	-	-	μs
Data Out Hold Time	t _{DH}	50	-	-	50	-	-	ns
Write Cycle Time	twR	ı	1.9	3	-	1.9	3	ms
5.0V, 25°C, Byte Mode (1)	Endurance	1M	-	-	1M	-	-	Write Cycles

^{(1):} This parameter is characterized and is not 100% tested.

Input pulse voltages: 0.3 V_{CC} to 0.7 V_{CC}

Input rise and fall time: 50ns

Input and output timing reference voltages: 0.5V_{CC}

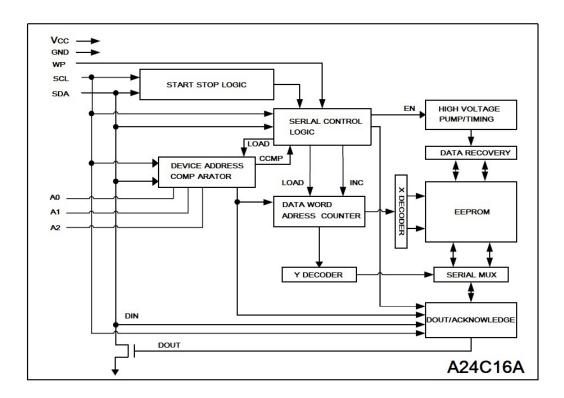
The value of $R_{\!\scriptscriptstyle L}$ should be concerned according to the actual loading on the user's system.

REV1.0Q - FEB 2024 RELEASED -

^{(2):} AC measurement conditions: R_L (connects to V_{CC}): 1.3K



BLOCK DIAGRAM



DETAILED INFORMATION

SERIAL DATA (SDA): The SDA pin is bi-directional for serial data transfer. This pin is open-drain driven and may be wire-OR 'ed with any number of other open-drain or open- collector devices.

SERIAL CLOCK (SCL): The SCL input is used to positive edge clock data into each EEPROM device and negative edge clock data out of each device.

WRITE PROTECT (WP): The A24C16A has a Write Protect pin that provides hardware data protection. The Write Protect pin allows normal read/write operations when connected to ground (GND). When the Write Protection pin is connected to V_{CC}, the write protection feature is enabled and operates as shown in the following Table 1.

Table1: Write Protect

WP Pin Status	A24C16A			
At V _{CC}	Full (16K) Array			
At GND	Normal Read/Write Operations			

REV1.0Q - FEB 2024 RELEASED - -5-

AEC-Q MEMORY EEPROM

16K bits (2048 X 8) HIGH TEMPERATURE AND AUTOMOTIVE EEPROM

FUNCTION DESCRIPTION

1.Memory Organization

A24C16A, 16K SERIAL EEPROM: Internally organized with 128 pages of 16 bytes each, the 16K requires an 11-bit data word address for random word addressing.

2. Device Operation

CLOCK and DATA TRANSITIONS:

The SDA pin is normally pulled high with an external device. Data on the SDA pin may change only during SCL low time periods (see Figure 1). Data changes during SCL high periods will indicate a start or stop condition as defined.

START CONDITION: A high-to-low transition of SDA with SCL high is a start condition which must precede any other command (see Figure 2).

STOP CONDITION: A low-to-high transition of SDA with SCL high is a stop condition. After a read sequence, the stop command will place the EEPROM in a standby power mode (see Figure 2).

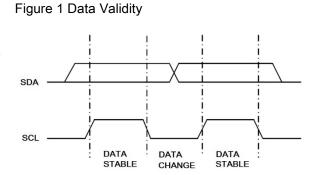
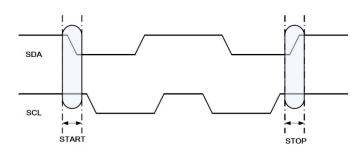


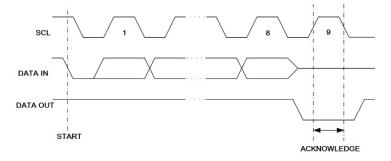
Figure 2 Start and Stop Definition



ACKNOWLEDGE:

All addresses and data words are serially transmitted to and from the EEPROM in 8-bit words. The EEPROM sends a "0" to acknowledge that it has received each word. This happens during the ninth clock cycle.

Figure 3 Output Acknowledge



REV1.0Q - FEB 2024 RELEASED - - 6 -

A24C16A
AEC-Q MEMORY EEPROM

16K bits (2048 X 8) HIGH TEMPERATURE AND AUTOMOTIVE EEPROM

STANDBY MODE: The A24C16A features a low-power standby mode which is enabled:

- (a) Upon power-up
- (b) After the receipt of the STOP bit and the completion of any internal operations.

MEMORY RESET: After the protocol is interrupted, power loss or system reset, any two-wire part can be reset by following these steps:

- 1. Clock up to 9 cycles.
- 2. Look for SDA high in each cycle while SCL is high.
- 3. Create a start condition and a stop condition.

3. Device Addressing

The 16K EEPROM devices all require an 8-bit device address word following a start condition to enable the chip for a read or write operation (see Figure 4).

Figure 4 Device Address

MSB							LSB
1	0	1	0	B10	В9	B8	R/W

The device address word consists of a mandatory "1", "0" sequence for the first four most significant bits as shown. This is common to all the Serial EEPROM devices. The 16K does not use any device address bits but instead the 3 bits are used for memory page addressing. These page addressing bits on the 16K devices should be considered the most significant bits of the data word address which follows.

The eighth bit of the device address is the read/write operation select bit. A read operation is initiated if this bit is high and a write operation is initiated if this bit is low.

Upon a compare of the device address, the EEPROM will output a "0". If a compare is not made, the chip will return to a standby state.

4. Write Operations

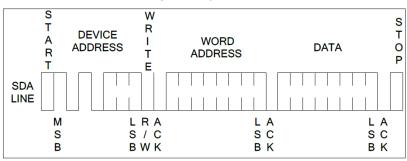
BYTE WRITE: A write operation requires an 8-bit data word address following the device address word and acknowledgment. Upon receipt of this address, the EEPROM will again respond with a "0" and then clock in the first 8-bit data word. Following receipt of the 8-bit data word, the EEPROM will output a "0" and the addressing device, such as a microcontroller, must terminate the write sequence with a stop condition. At this time the EEPROM enters an internally timed write cycle, twR, to the nonvolatile memory. All inputs are disabled during this write cycle and the EEPROM will not respond until the write is complete (see Figure 5).

REV1.0Q - FEB 2024 RELEASED - - 7 -

AEC-Q MEMORY EEPROM

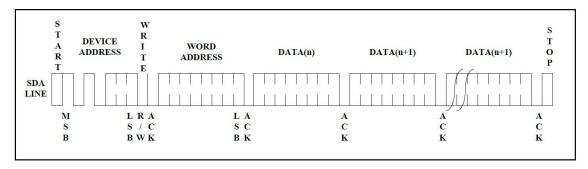
16K bits (2048 X 8) HIGH TEMPERATURE AND AUTOMOTIVE EEPROM





PAGE WRITE: A page write is initiated the same as a byte write, but the microcontroller does not send a stop condition after the first data word is clocked in. Instead, after the EEPROM acknowledges receipt of the first data word, the microcontroller can transmit up to fifteen more data words. The EEPROM will respond with a "0" after each data word received. The microcontroller must terminate the page write sequence with a stop condition (see Figure 6).

Figure 6 Page Write



The data word address lower four bits are internally incremented following the receipt of each data word. The higher data word address bits are not incremented, retaining the memory page row location. When the word address, internally generated, reaches the page boundary, the following byte is placed at the beginning of the same page. If more than sixteen data words are transmitted to the EEPROM, the data word address will "roll over" and previous data will be overwritten.

ACKNOWLEDGE POLLING: Once the internally timed write cycle has started and the EEPROM inputs are disabled, acknowledge polling can be initiated. This involves sending a start condition followed by the device address word. The read/write bit is representative of the operation desired. Only if the internal write cycle has completed will the EEPROM respond with a "0", allowing the read or write sequence to continue.

REV1.0Q - FEB 2024 RELEASED - - 8 -

AEC-Q MEMORY EEPROM

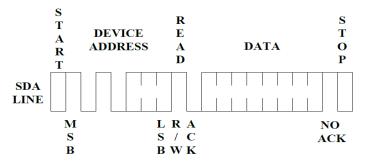
16K bits (2048 X 8) HIGH TEMPERATURE AND AUTOMOTIVE EEPROM

5.Read Operations

Read operations are initiated the same way as write operations with the exception that the read/write select bit in the device address word is set to "1". There are three read operations: current address read, random address read and sequential read.

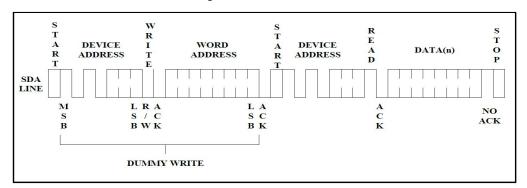
CURRENT ADDRESS READ: The internal data word address counter maintains the last address accessed during the last read or write operation, incremented by one. This address stays valid between operations as long as the chip power is maintained. The address "roll over" during read is from the last byte of the last memory page to the first byte of the first page. The address "roll over" during write is from the last byte of the current page to the first byte of the same page. Once the device address with the read/write select bit set to "1" is clocked in and acknowledged by the EEPROM, the current address data word is serially clocked out. The microcontroller does not respond with an input "0" but does generate a following stop condition (see Figure 7).

Figure 7 Current Address Read



RANDOM READ: A random read requires a "dummy" byte write sequence to load in the data word address. Once the device address word and data word address are clocked in and acknowledged by the EEPROM, the microcontroller must generate another start condition. The microcontroller now initiates a current address read by sending a device address with the read/write select bit high. The EEPROM acknowledges the device address and serially clocks out the data word. The microcontroller does not respond with a "0" but does generate a following stop condition (see Figure 8)

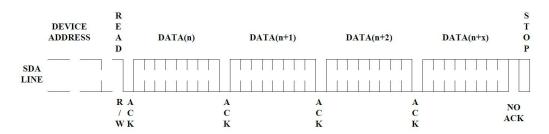
Figure 8 Random Read



REV1.0Q - FEB 2024 RELEASED - - 9 -

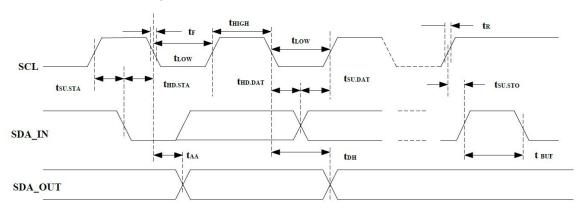
SEQUENTIAL READ: Sequential reads are initiated by either a current address read or a random address read. After the microcontroller receives a data word, it responds with an acknowledge. As long as the EEPROM receives an acknowledge, it will continue to increment the data word address and serially clock out sequential data words. When the memory address limit is reached, the data word address will "roll over" and the sequential read will continue. The sequential read operation is terminated when the microcontroller does not respond with a "0" but does generate a following stop condition (see Figure 9).

Figure 9 Sequential Read



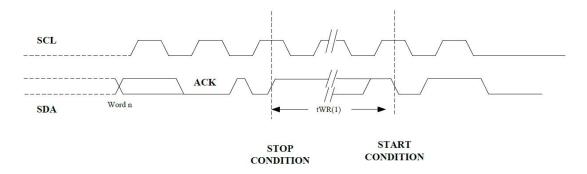
BUS TIMING

Figure 10 SCL: Serial Clock, SDA: Serial Data I/O



WRITE CYCLE TIMING

Figure 11 SCL: Serial Clock, SDA: Serial Data I/O

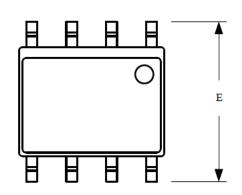


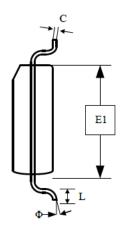
NOTE: The write cycle time twee is the time from a valid stop condition of a write sequence to the end of the internal clear/write cycle.

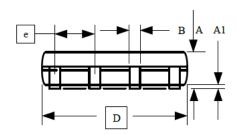
REV1.0Q - FEB 2024 RELEASED - - 10 -

PACKAGE INFORMATION

Dimension in SOP8 (Unit: mm)





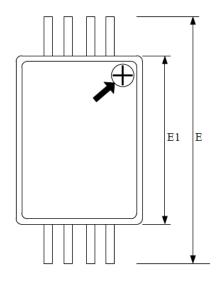


Symbol	Min	Max
А	1.350	1.750
A1	0.100	0.230
В	0.390	0.480
С	0.210	0.260
D	4.700	5.100
E1	3.700	4.100
E	5.800	6.200
е	1.27	BSC
L	0.500	0.800
θ	0°	8°

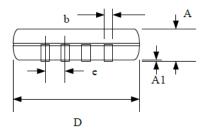
REV1.0Q - FEB 2024 RELEASED -- 11 -

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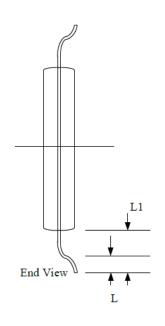
Dimension in TSSOP8 Package (Unit: mm)



Top View



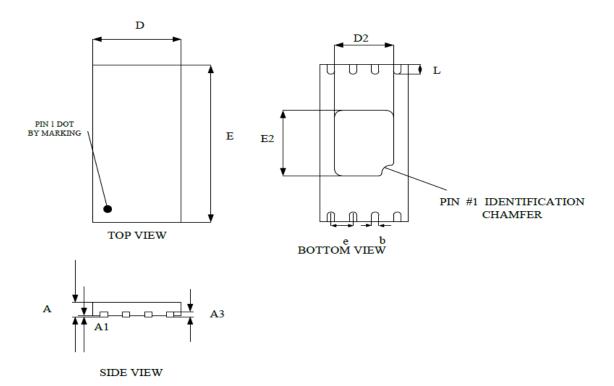
Side View



Symbol	Min	Max		
D	2.900	3.100		
Е	6.200	6.600		
E1	4.300	4.500		
Α	-	1.200		
A1	0.050	0.150		
b	0.210	0.300		
е	0.650 BSC			
L	0.450	0.750		
L1	1.000 REF			

REV1.0Q - FEB 2024 RELEASED - - 12 -

Dimension in DFN8 (Unit: mm)

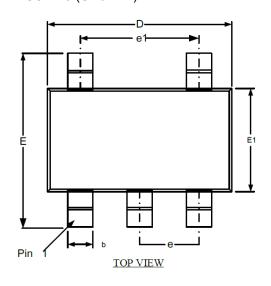


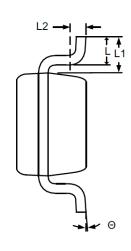
Symbol	Min	Max
Α	0.500	0.600
A1	0.000	0.050
A3	0.15 REF	
D	1.950	2.050
E	2.950	3.050
b	0.200	0.300
L	0.200	0.400
D2	1.250	1.500
E2	1.150	1.400
е	0.500 BSC	

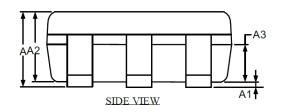
REV1.0Q - FEB 2024 RELEASED - - 13 -

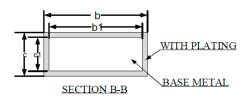


Dimension in SOT-25 (Unit: mm)







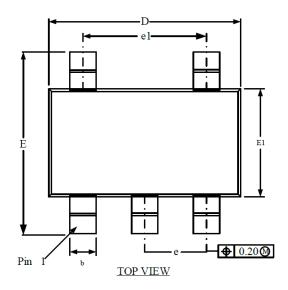


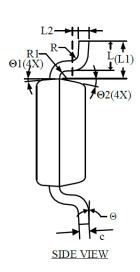
Symbol	Min.	Max.
Α	-	1.350
A1	0.040	0.150
A2	1.000	1.200
A3	0.550	0.750
b	0.380	0.480
b1	0.370	0.430
С	0.110	0.210
c1	0.100	0.160
D	2.720	3.120
Е	2.600	3.000
E1	1.400	1.800
е	0.950 BSC	
e1	1.900 BSC	
L	0.300	0.600
L1	0.575 REF	
L2	0.258 BSC	
θ	0°	8°

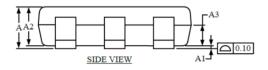
REV1.0Q - FEB 2024 RELEASED - - 14 -



Dimension in TSOT-25 (Unit: mm)







Symbol	Min	Max
Α	-	0.900
A1	0.000	0.100
A2	0.650	0.850
A3	0.350	0.450
b	0.300	0.500
С	0.140	0.200
D	2.850	3.050
Е	2.650	2.950
E1	1.600	1.700
е	0.900	1.000
e1	1.800	2.000
L	0.300	0.600
L1	0.575 REF	
L2	0.258 BSC	
R	-	0.25
R1	-	0.25
θ	0°	8°
θ1	3°	7°
θ2	10°	14°

REV1.0Q - FEB 2024 RELEASED -- 15 -

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REV1.0Q - FEB 2024 RELEASED - - 16 -